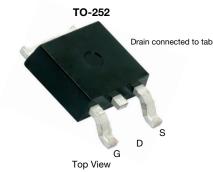


www.vishay.com Vishay Siliconix

# N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) MAX.	I <sub>D</sub> (A) °	Q <sub>g</sub> (TYP.)	
100	0.0089 at V <sub>GS</sub> = 10 V	50	33 nC	
100	0.0093 at V <sub>GS</sub> = 7.5 V	50	33 110	



#### **Ordering Information:**

SUD70090E-GE3 (lead (Pb)-free and halogen-free)

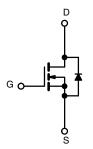
#### **FEATURES**

- ThunderFET® power MOSFET
- Maximum 175 °C junction temperature
- Q<sub>gd</sub> / Q<sub>gs</sub> ratio < 1 optimizes switching characteristics
- 100 % R<sub>g</sub> and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **APPLICATIONS**

- DC/DC converter
- Power tools
- · Motor drive switch
- DC/AC inverter
- Battery management





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	100	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	7 v
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C	,	50 °	
	T <sub>C</sub> = 70 °C	I <sub>D</sub>	50 °	
Pulsed Drain Current (t = 100 μs)		I <sub>DM</sub>	120	Α
Avalanche Current		I <sub>AS</sub>	40	
Single Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	80	mJ
M	T <sub>C</sub> = 25 °C	Б	125	- w
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 70 °C b	P <sub>D</sub>	87.5	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) <sup>b</sup>	R <sub>thJA</sub>	40	°C/W
Junction-to-Case (Drain)	R <sub>thJC</sub>	1.2	]

#### Notes

- a. Duty cycle ≤ 1 %.
- b. When mounted on 1" square PCB (FR4 material).
- c. Package limited.



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_D=250\;\mu A$	2	-	4	V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 250	nA
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	-	-	1	- μΑ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ = 100 V, $V_{GS}$ = 0 V, $T_J$ = 125 °C	-	-	150	
		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$	-	-	5	mA
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	50	-	-	Α
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	-	0.0074	0.0089	0
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 7.5 V, I <sub>D</sub> = 15 A	-	0.0077	0.0093	Ω
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A	-	38	-	S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>		-	1950	-	pF
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}$	-	845	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	54	-	
Total Gate Charge <sup>c</sup>	Qg		-	33	50	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	8.8	-	nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$		-	7.5	-	
Gate Resistance	$R_g$	f = 1 MHz	0.7	3.5	7	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		-	15	30	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 50 \text{ V}, R_L = 5 \Omega$	-	27	54	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	36	72	ns
Fall Time <sup>c</sup>	t <sub>f</sub>		-	45	90	
Drain-Source Body Diode Ratings ar	nd Characteri	stics <sup>b</sup> (T <sub>C</sub> = 25 °C)				
Pulsed Current (t = 100 μs)	I <sub>SM</sub>		-	-	120	Α
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V	-	0.8	1.5	V
Reverse Recovery Time	t <sub>rr</sub>		-	77	116	ns
Peak Reverse Recovery Charge	I <sub>RM(REC)</sub>	$I_F = -10 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$	-	4.2	6.3	Α
Reverse Recovery Charge	Q <sub>rr</sub>		-	145	365	nC

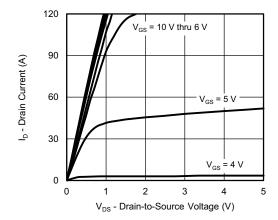
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

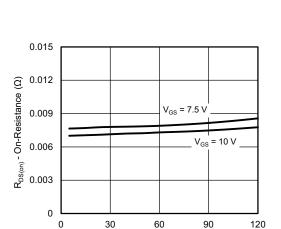
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

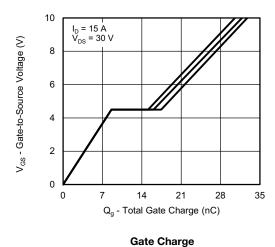


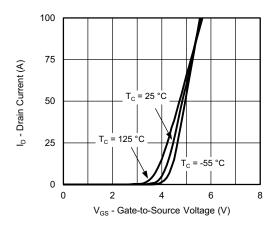
#### **Output Characteristics**



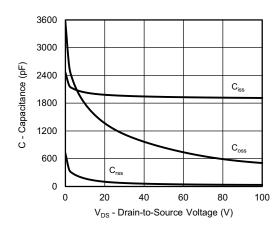
On-Resistance vs. Drain Current

I<sub>D</sub> - Drain Current (A)

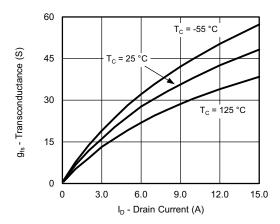




**Transfer Characteristics** 



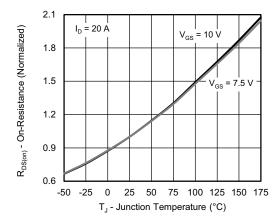
Capacitance



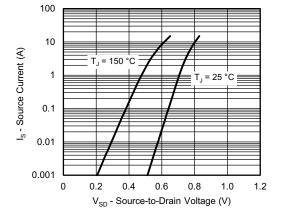
Transconductance



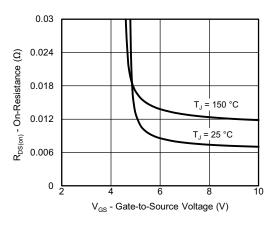
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



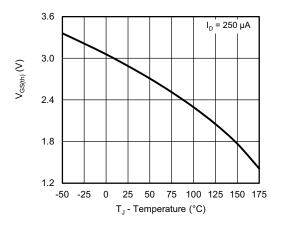
On-Resistance vs. Junction Temperature



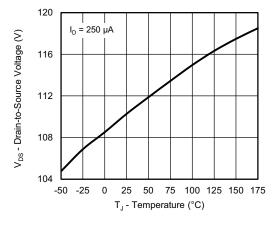
**Source Drain Diode Forward Voltage** 



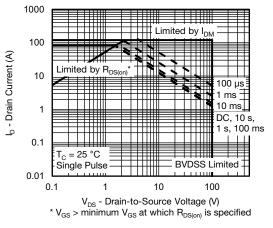
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



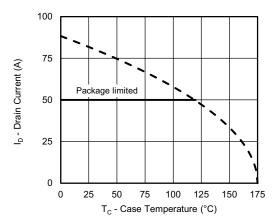
**Drain Source Voltage vs. Junction Temperature** 



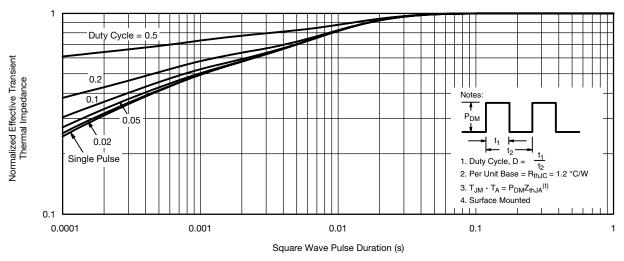
Safe Operating Area



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### **Current De-Rating**



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- · The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C)

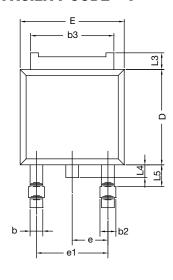
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

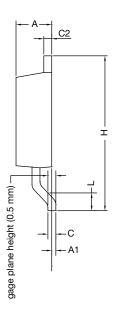
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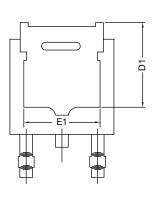


## **TO-252AA Case Outline**

### **VERSION 1: FACILITY CODE = Y**







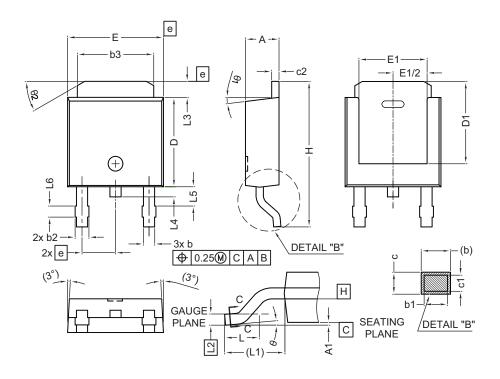
	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	2.18	2.38	
A1	-	0.127	
b	0.64	0.88	
b2	0.76	1.14	
b3	4.95	5.46	
С	0.46	0.61	
C2	0.46	0.89	
D	5.97	6.22	
D1	4.10	-	
E	6.35	6.73	
E1	4.32	=	
Н	9.40	10.41	
е	2.28 BSC		
e1	4.56 BSC		
L	1.40	1.78	
L3	0.89	1.27	
L4	-	- 1.02	
L5	1.01	1.52	

#### Note

• Dimension L3 is for reference only



#### **VERSION 2: FACILITY CODE = N**



	MILLIMETERS		
DIM.	MIN.	MAX.	
А	2.18	2.39	
A1	-	0.13	
b	0.65	0.89	
b1	0.64	0.79	
b2	0.76	1.13	
b3	4.95	5.46	
С	0.46	0.61	
c1	0.41	0.56	
c2	0.46	0.60	
D	5.97	6.22	
D1	5.21	-	
Е	6.35	6.73	
E1	4.32	-	
е	2.29 BSC		
Н	9.94	10.34	

	MILLIMETERS		
DIM.	MIN.	MAX.	
L	1.50	1.78	
L1	2.74 ref.		
L2	0.51 BSC		
L3	0.89	1.27	
L4	-	1.02	
L5	1.14	1.49	
L6	0.65	0.85	
θ	0°	10°	
θ1	0°	15°	
θ2	25°	35°	

#### Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022

DWG: 5347



## **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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